IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: :

Yong-Bae Kim and Philippe Schoenborn

Appl. No.

Continuation of 09/898,194

Filed:

Herewith

Title

PROCESS FOR REMOVAL OF PHOTORESIST MASK USED FOR MAKING VIAS IN LOW K CARBON-DOPED SILICON OXIDE DIFLECTRIC MATERIAL. AND FOR REMOVAL OF ETCH

DIELECTRIC MATERIAL, AND FOR REMOVAL OF ETCH RESIDUES FROM FORMATION OF VIAS AND REMOVAL OF

PHOTORESIST MASK

Grp./ A.U. :

1765

Examiner

Kin-Chan Chen

Docket No. :

01-125/1C

PRELIMINARY AMENDMENT

Honorable Commissioner for Patents Post Office Box 1450 Alexandria, VA 22313-1450

Date: July 14, 2003

Sir:

Please amend the accompanying continuation application as follows: